

Listing and Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A mask, comprising:

a mask substrate;
a half-tone layer of half-tone mask material arranged in a pattern across the mask substrate;
and
a light-blocking layer of light blocking material arranged in a pattern across the half-tone layer;
wherein the half-tone mask material is silicon-rich silicon nitride $\text{SiN}_x\text{:H}$ with x in the range 0 to 1, and wherein a thickness of the half-tone layer and x are selected to provided a transmittance in the range of 20% to 80%.

2. (Previously Presented) The mask of claim 1 wherein the silicon-rich silicon nitride layer has a value of x in the range 0.2 to 0.6 and an optical band gap of from 2.1eV to 2.5eV.

3. (Previously Presented) The mask of claim 1 wherein the silicon-rich silicon nitride layer has a thickness of from 40nm to 100nm.

4. (Withdrawn) Use of the mask of claim 1 including exposing a layer of photoresist by passing ultra-violet light through the mask onto the layer of photoresist to define fully removed regions in which the photoresist is fully removed, thick regions having a first thickness and thin regions having a thickness less than the first thickness in the regions exposed through the half-tone regions.

5-8. (Cancelled)

9. (Previously Presented) The mask of claim 1 wherein the silicon-rich silicon nitride layer has a value of x in the range 0.2 to 0.5 and an optical band gap of from 2.1eV to 2.35eV.

10. (Previously Presented) The mask of claim 1 wherein the silicon-rich silicon nitride layer has a thickness of 60nm and an optical band gap of 2.3eV.

11. **(Previously Presented)** The mask of claim 1 wherein the thickness of the half-tone layer and x are selected to provided a transmittance in the range of 40% to 80%.

12. **(New)** The mask as defined in claim 1 wherein variation of the thickness of the half-tone layer is less than or equal to 20%.